

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor structure comprising:

an island of a semiconductor material, said island including a plurality of sidewalls and a strained region;
a handle wafer; and
an insulating layer disposed between said island and said handle wafer, said insulating layer containing a thickened region underlying said strained region, said insulating layer electrically isolating said island of said semiconductor material from said handle wafer, and said thickened region transferring tensile stress to said strained region.

2. (Previously Presented) The semiconductor structure of claim 1 wherein said insulating layer is a buried oxide layer and said island is silicon.

3. (Previously Presented) The semiconductor structure of claim 1 further comprising:

a source defined in said island;
a drain defined in said island; and
a channel defined in a portion of said island between said source and said drain, said channel disposed at least partially in said strained region of said island.

4. (Previously Presented) The semiconductor structure of claim 3 further comprising:
 - a gate electrode electrically isolated from said portion of said island defining said channel.
5. (Original) The semiconductor structure of claim 4 wherein said strained region divides said gate electrode.
6. (Original) The semiconductor structure of claim 4 wherein said gate electrode generally overlies said channel.
7. (Previously Presented) The semiconductor structure of claim 1 further comprising:
 - a semiconductor device fabricated using said island.
8. (Previously Presented) The semiconductor structure of claim 1 wherein said island is silicon and said thickened region of said insulating layer is formed by oxidation of said island.
9. (Original) The semiconductor structure of claim 9 wherein said insulating layer is silicon dioxide.
10. (Previously Presented) The semiconductor structure of claim 9 wherein said handle wafer is silicon and said thickened region is formed by oxidation of said handle wafer.
11. (Original) The semiconductor structure of claim 1 wherein said tensile stress is effective to enhance carrier mobility within said strained region.
12. (Original) The semiconductor structure of claim 1 wherein a thickness of said thickened region is increased by an increment in the range of about 5 nanometers to about 10 nanometers.

13. (Original) The semiconductor structure of claim 1 wherein said thickened region of said insulating layer has a thickness greater than that of surrounding regions of said insulating layer flanking said thickened region.

14. (Previously Presented) The semiconductor structure of claim 1 further comprising:
first and second anchors flanking said strained region, said first and second anchors effective for limiting relaxation of said strained region of said island.

15. (Currently Amended) The semiconductor structure of claim [[16]] 14 wherein said first and second anchors comprise adjacent regions of said island flanking said strained region.

16-34. (Cancelled)